

ABSTRACT

The present invention relates to a method for fabricating a semiconductor device. The method comprises the steps of: 1. A method for fabricating a semiconductor device, which comprises the steps of: forming a gate line on a semiconductor substrate; forming junction regions in the semiconductor substrate at both sides of the gate line; forming and selectively removing an interlayer insulating film on the substrate to form contact holes exposing the junction regions; forming plugs in the contact holes; and implanting impurity ions into the plugs; and annealing the junction regions.